TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

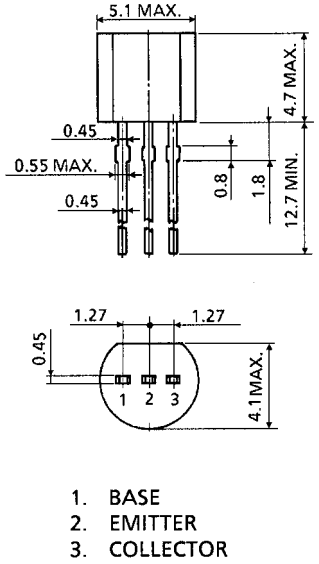
2SC3605

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

Unit in mm

FEATURES:

- Low Noise Figure, High Gain
- NF = 1.1dB, $|S_{21e}|^2$ = 10dB (f = 1GHz)



1. BASE
2. EMITTER
3. COLLECTOR

JEDEC	TO−92
EIAJ	SC−43
TOSHIBA	2−5F1E

Weight: 0.21g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current	I_C	80	mA
Base Current	I_B	40	mA
Collector Power Dissipation	P_C	600	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Transition Frequency	f_T	V_{CE} = 10V, I_C = 20mA	5	6.5	—	GHz
Insertion Gain	$\|S_{21e}\|^2$ (1)	V_{CE} = 10V, I_C = 20mA, f = 500MHz	—	16	—	dB
	$\|S_{21e}\|^2$ (2)	V_{CE} = 10V, I_C = 20mA, f = 1GHz	7.5	10	—	
Noise Figure	NF (1)	V_{CE} = 10V, I_C = 5mA, f = 1GHz	—	1.1	—	dB
	NF (2)	V_{CE} = 10V, I_C = 40mA, f = 1GHz	—	1.8	3	

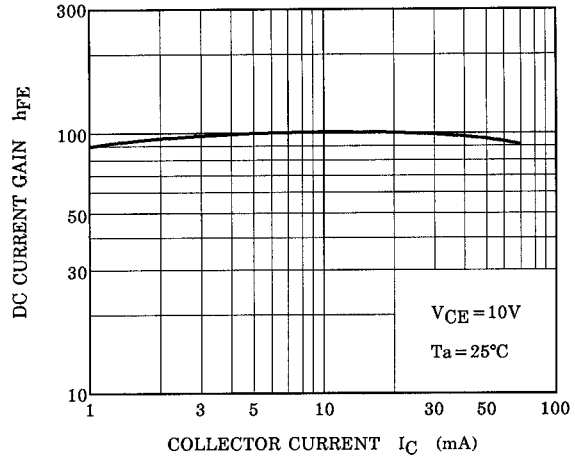
000707EAA1

ELECTRICAL CHARACTERISTICS (Ta=25°C)

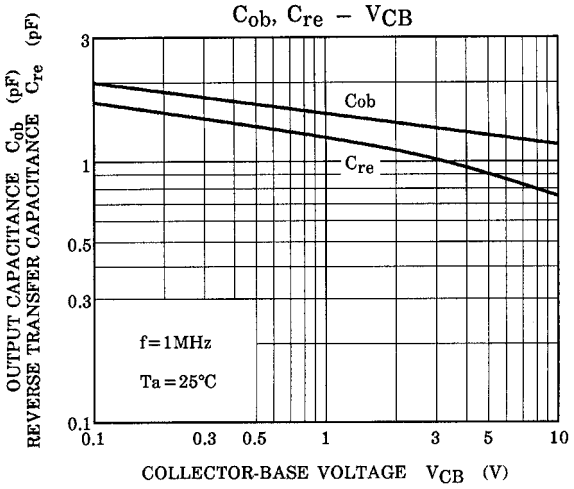
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Collector Cut-off Current	I_{CBO}	V_{CE} = 10V, I_E = 0	—	—	1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 1V, I_E = 0	—	—	1	μA
DC Current Gain	h_{FE}	V_{CE} = 10V, I_C = 20mA	30	—	250	—
Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz (Note)	—	1.2	—	pF
Reverse Transfer Capacitance	C_{re}		—	0.75	1.2	pF

Note: C_{re} is measured by 3−terminal method with Capacitance Bridge.

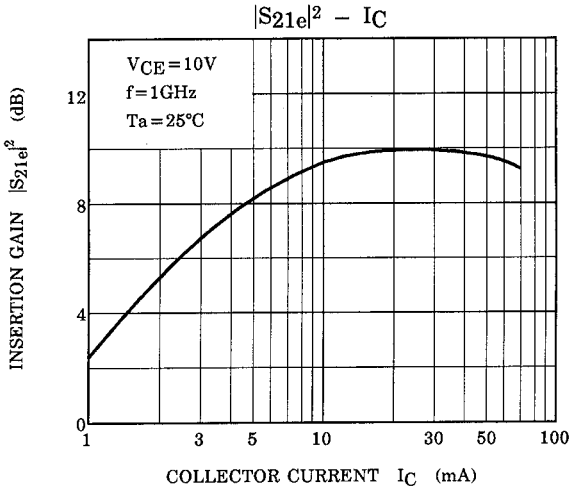
h_{FE} – I_C



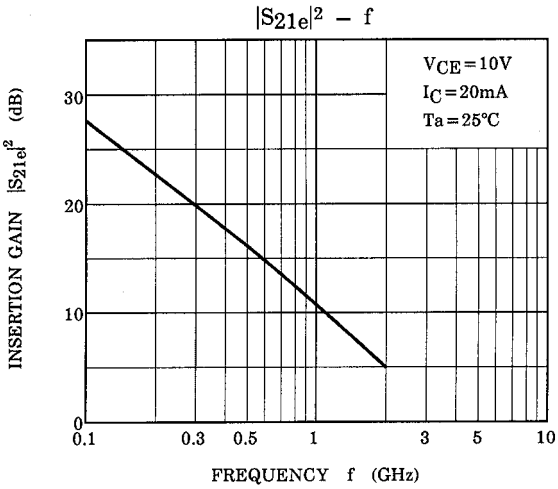
C_{ob}, C_{re} – V_{CB}



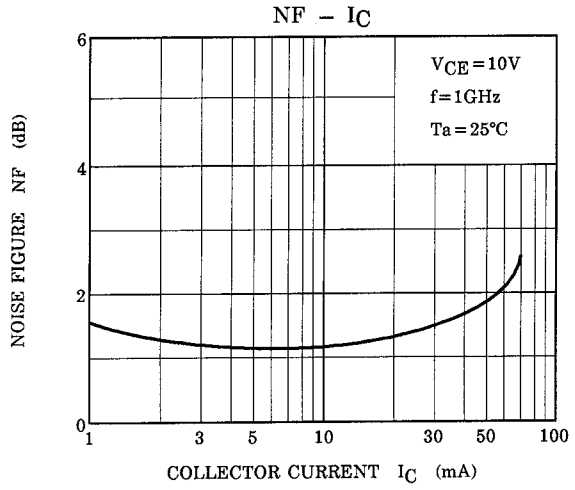
$|S_{21e}|^2$ – I_C



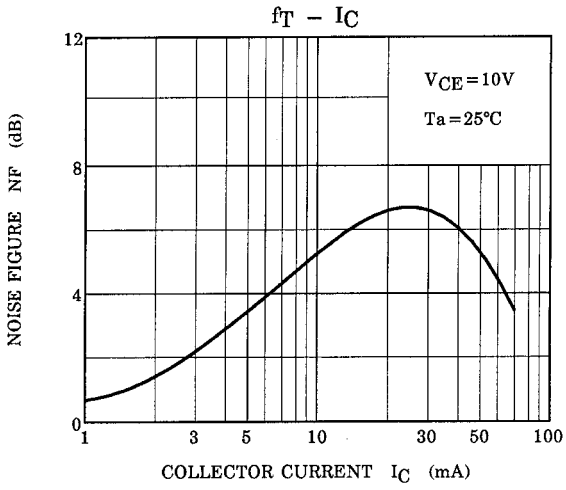
$|S_{21e}|^2$ – f

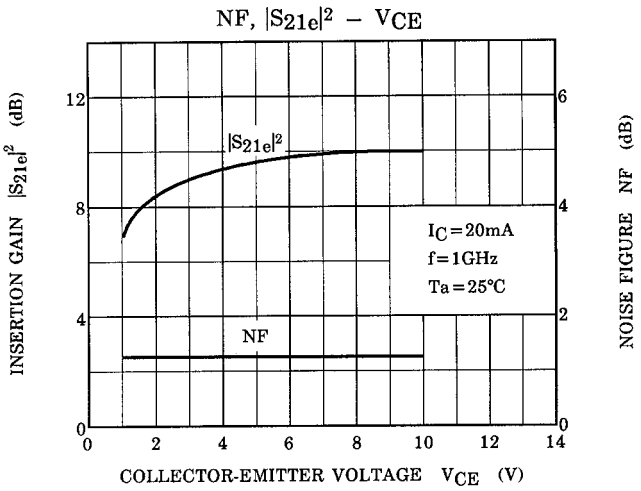


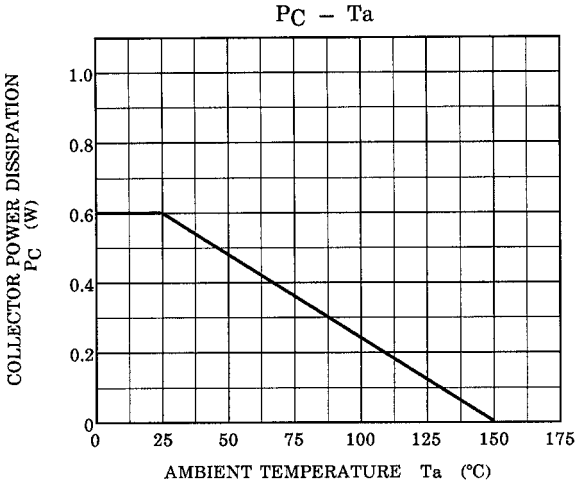
NF – I_C



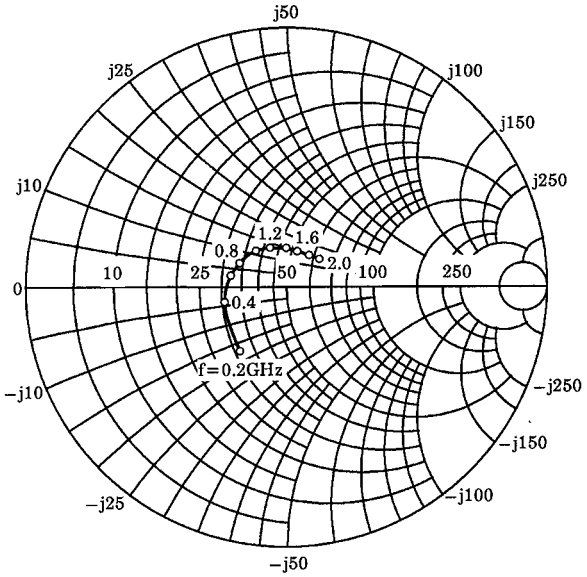
f_T – I_C



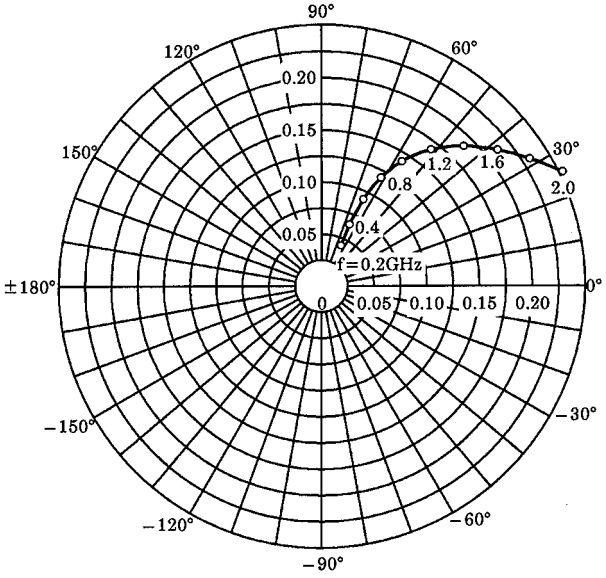

NF, $|S_{21e}|^2$ – V_{CE}
INSERTION GAIN $|S_{21e}|^2$ (dB)
NOISE FIGURE NF (dB)
$|S_{21e}|^2$
NF
I_C = 20mA
f = 1GHz
Ta = 25°C
COLLECTOR-EMITTER VOLTAGE V_{CE} (V)


P_C – Ta
COLLECTOR POWER DISSIPATION P_C (W)
AMBIENT TEMPERATURE Ta (°C)

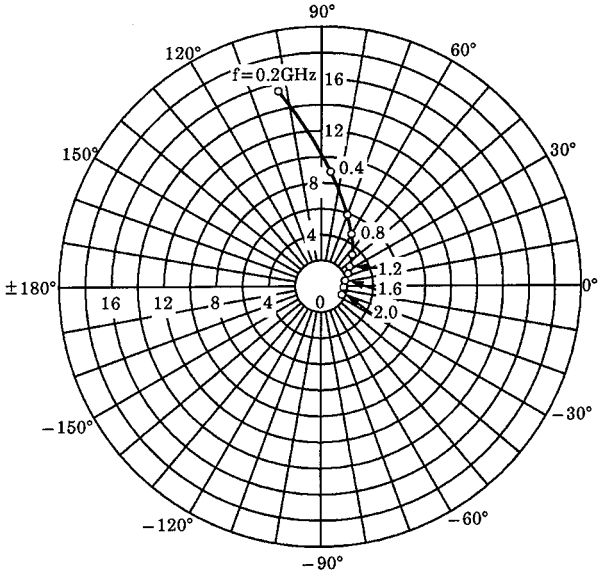
S_{11e}
V_{CE} = 10V
I_C = 20mA
Ta = 25°C
(UNIT : Ω)



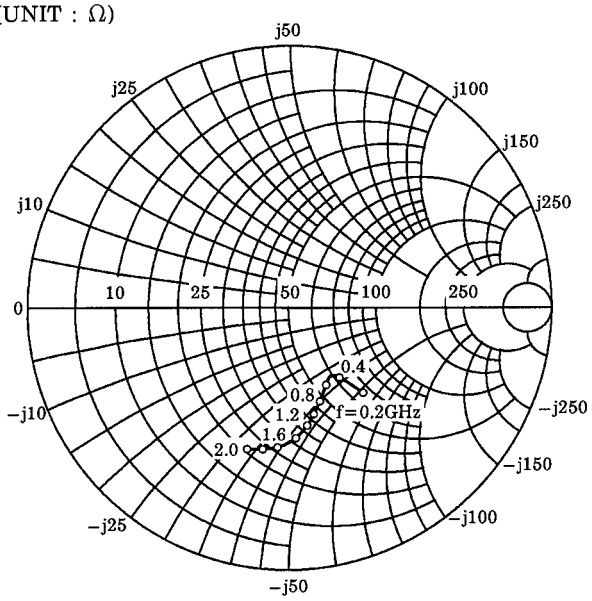
S_{12e}
V_{CE} = 10V
I_C = 20mA
Ta = 25°C



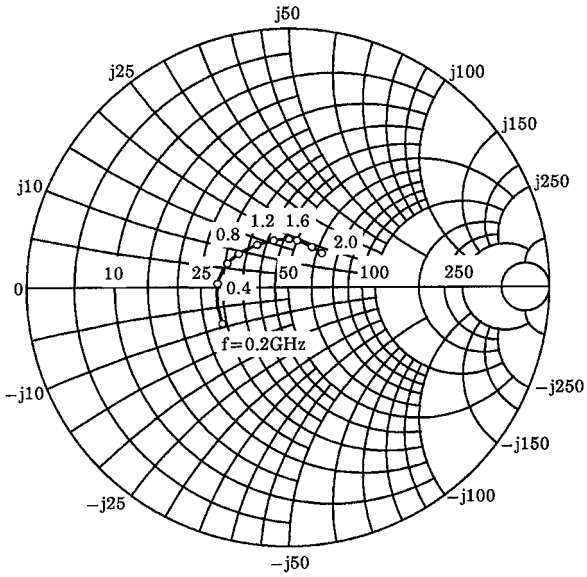
S_{21e}
V_{CE} = 10V
I_C = 20mA
Ta = 25°C



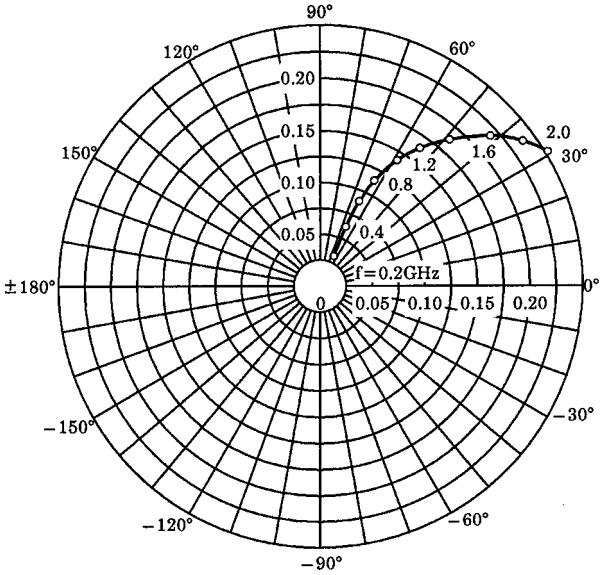
S_{22e}
V_{CE} = 10V
I_C = 20mA
Ta = 25°C
(UNIT : Ω)



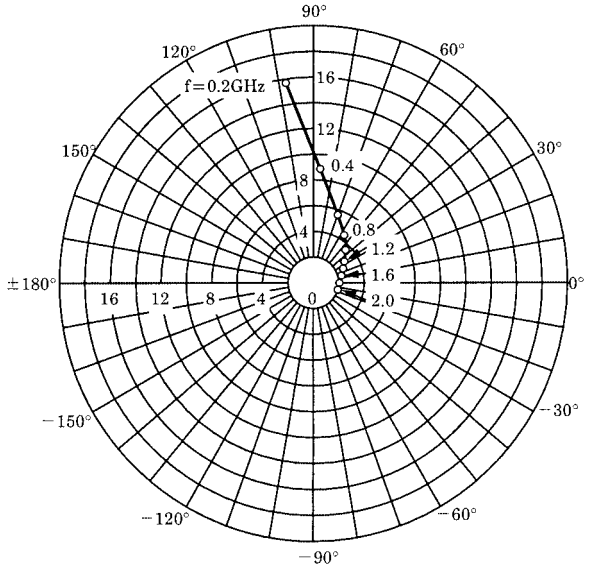
S_{11e}
V_{CE} = 10V
I_C = 40mA
Ta = 25°C
(UNIT : Ω)



S_{12e}
V_{CE} = 10V
I_C = 40mA
Ta = 25°C



S_{21e}
V_{CE} = 10V
I_C = 40mA
Ta = 25°C



S_{22e}
V_{CE} = 10V
I_C = 40mA
Ta = 25°C
(UNIT : Ω)